■ **Electrical Characteristics** (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250μA	60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=60V, V_{GS}				

Typical Electrical and Thermal Characteristics Diagrams

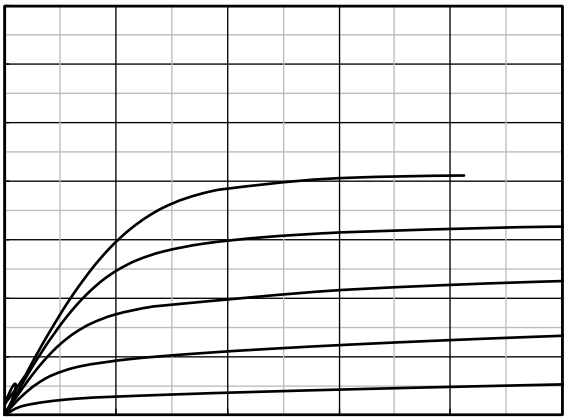


Figure 1. Output Characteristics

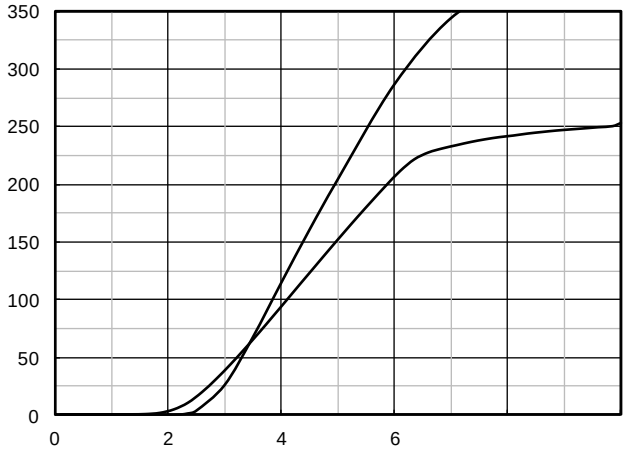


Figure 2. Transfer Characteristics

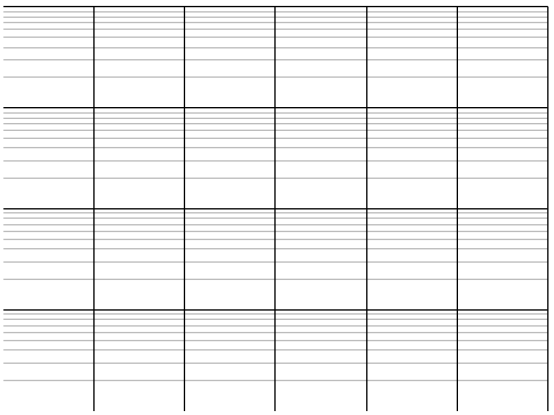


Figure 3. Capacitance Characteristics

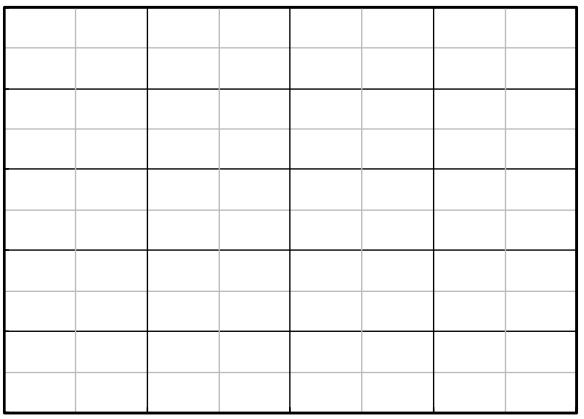
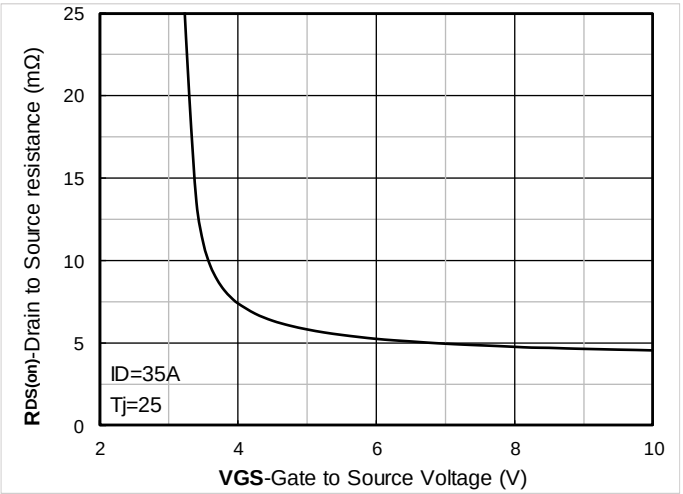


Figure 4. Gate Charge



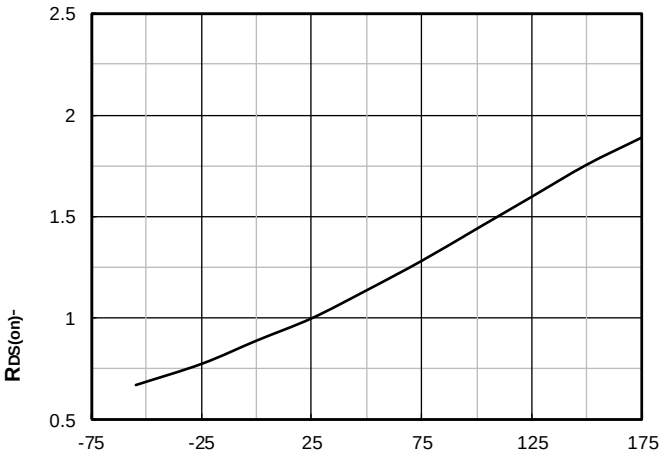


Figure 5.

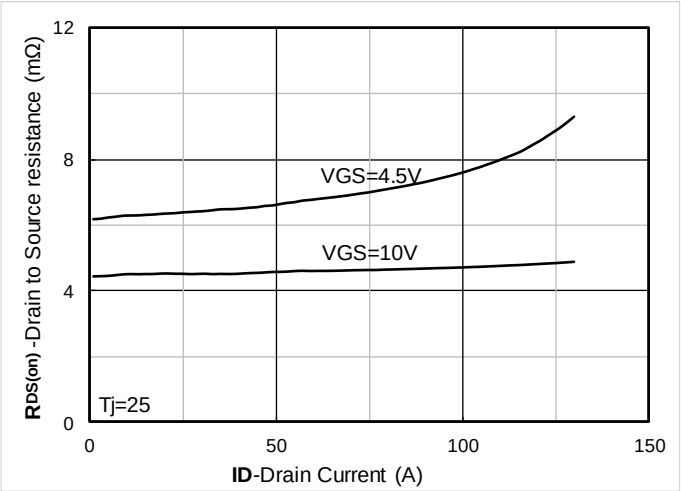


Figure 7. $R_{DS(on)}$ VS Drain Current

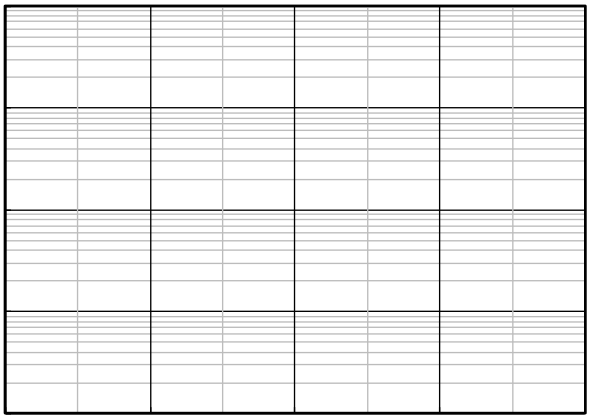
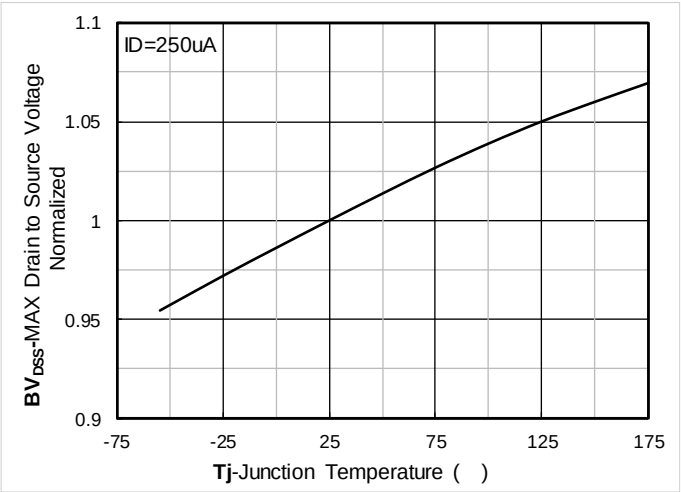


Figure 8. Forward characteristics of reverse diode



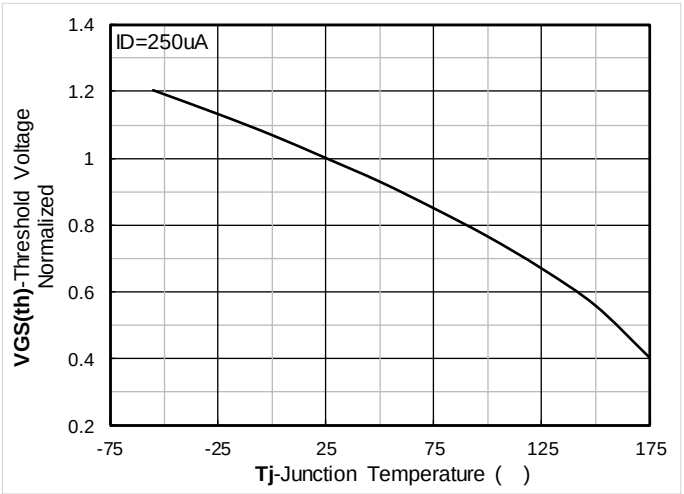


Figure 9. Normalized breakdown v8821Q EMC /P #MCID 4/Lang (en6 355ag0008882 0 596.04 842.04 reW* nBT/F5 9

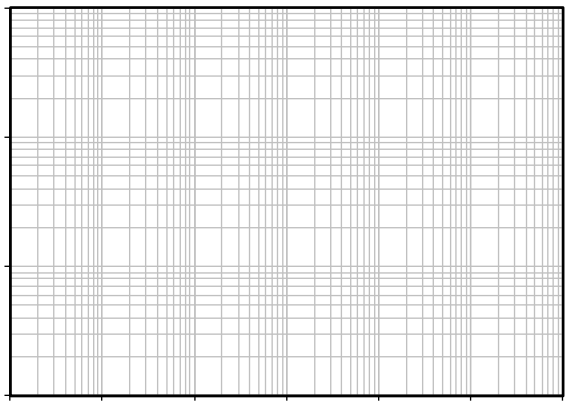


Figure 13. Maximum Transient Thermal Impedance

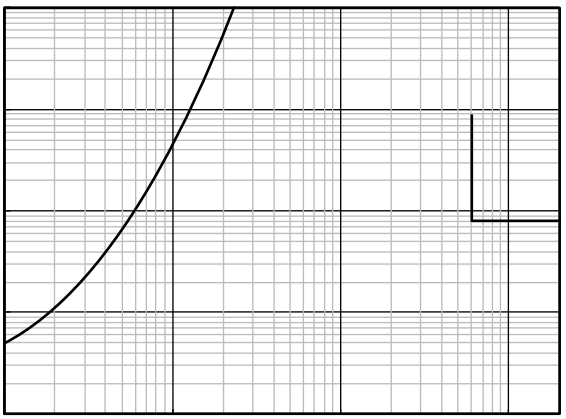


Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

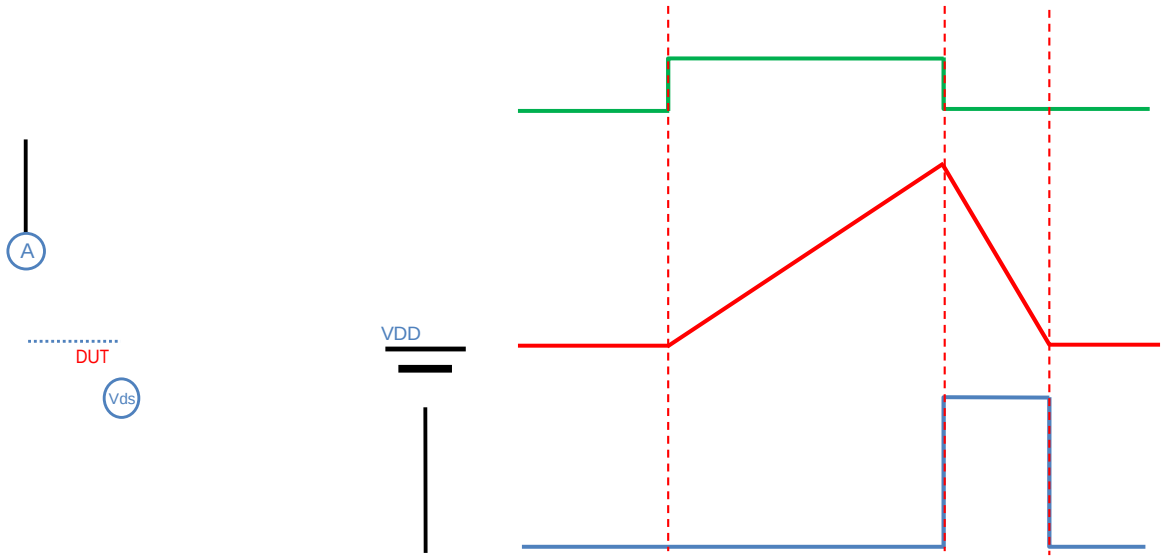
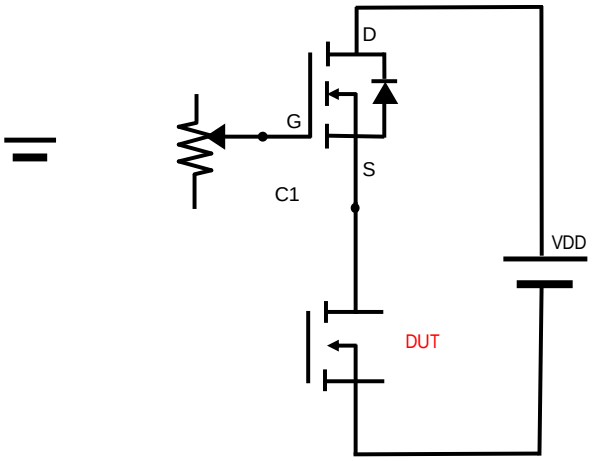
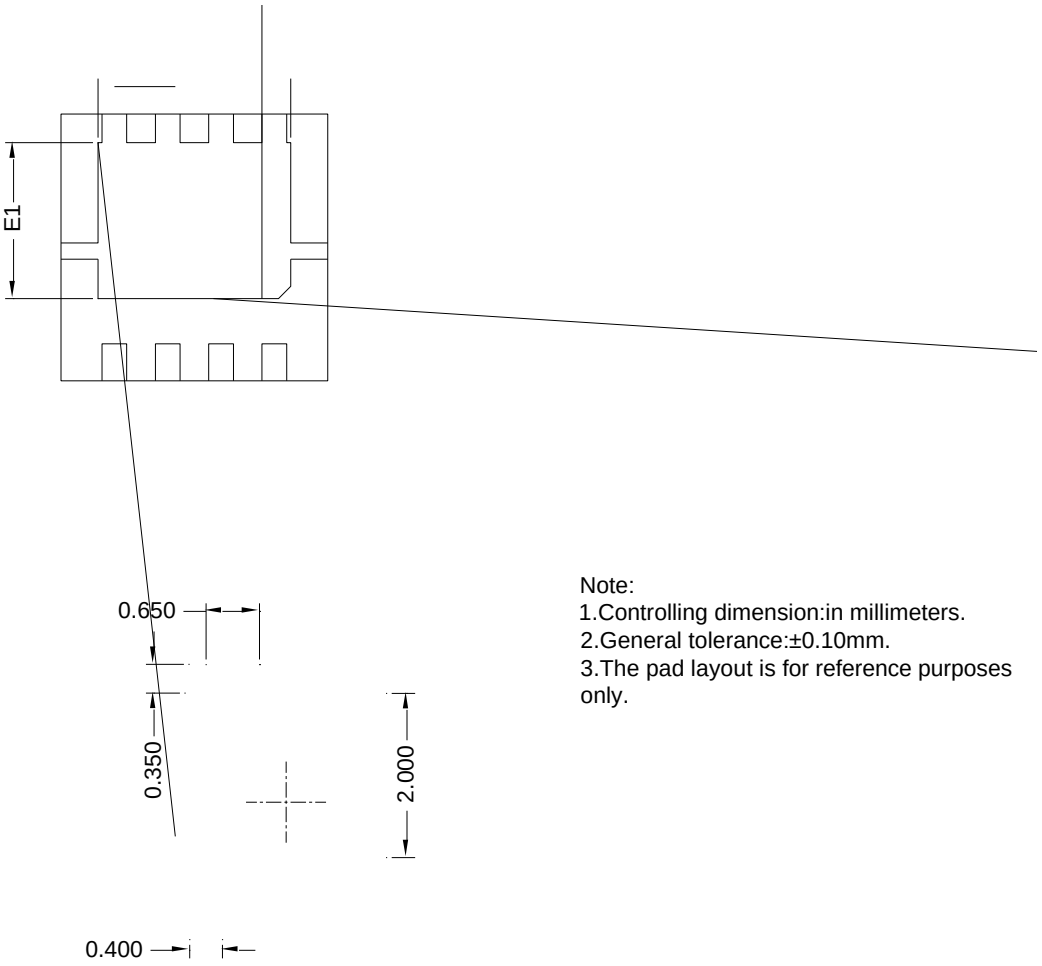


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform


D
G
S
C1
VDD
DUT

■ DFN3333-8L-A-0.8MM Package information



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.10mm.
3.The pad layout is for reference purposes only.

Suggested Solder Pad Layout
Top View

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